2SJ117

Silicon P-Channel MOS FET

HITACHI

ADE-208-1180 (Z) 1st. Edition Mar. 2001

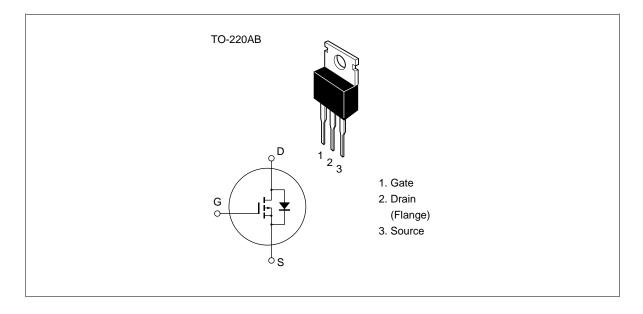
Application

High speed power switching

Features

- High speed switching
- Good frequency characteristics
- Wide area of safe operation
- Suitable for switching regulator, DC-DC converter and ultrasonic power oscillators.

Outline





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Absolute Maximum Ratings (Ta = 25°C)

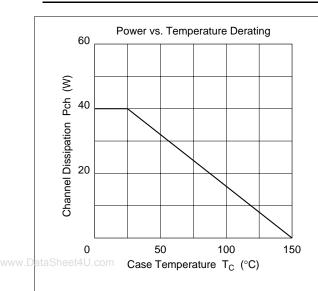
Item	Symbol	Ratings	Unit
Drain to source voltage	$V_{ t DSS}$	-400	V
Gate to source voltage	V _{GSS}	±20	V
Drain current	I _D	-2	A
Drain peak current	I D(pulse)	-4	А
Body to drain diode reverse drain current	I _{DR}	-2	А
Channel dissipation	Pch*1	40	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

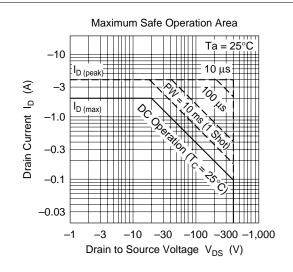
Notes: 1. Value at T_c = 25°C www.DataSheet4U.com

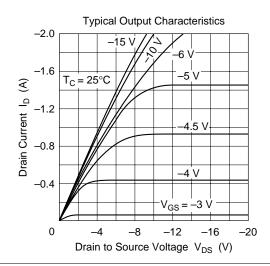
Electrical Characteristics ($Ta = 25^{\circ}C$)

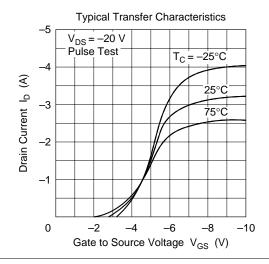
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	-400	_	_	V	$I_{D} = -10 \text{ mA}, V_{GS} = 0$
Gate to source leak current	I _{GSS}	_	_	±1	μΑ	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I _{DSS}	_	_	-1	mA	$V_{DS} = -320 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{\text{GS(off)}}$	-2.0	_	-5.0	V	$I_D = -1 \text{ mA}, V_{DS} = -10 \text{ V}$
Static drain to source on state	R _{DS(on)}	_	5	7		$I_D = -1 \text{ A}, V_{GS} = -15 \text{ V}^{*1}$
resistance						
Forward transfer admittance	$ y_{fs} $	0.4	0.7	_	S	$I_D = -1 \text{ A}, V_{DS} = -20 \text{ V}^{*1}$
Input capacitance	Ciss	_	520	_	pF	$V_{DS} = -10 \text{ V}, V_{GS} = 0,$
Output capacitance	Coss	_	110	_	pF	f = 1 MHz
Reverse transfer capacitance	Crss	_	15	_	pF	
Turn-on delay time	t _{d(on)}	_	10	_	ns	$I_D = -2 \text{ A}, V_{GS} = -15 \text{ V},$
Rise time	t _r	_	25	_	ns	R _L = 15
Turn-off delay time	t _{d(off)}	_	45	_	ns	
Fall time	t _f	_	35	_	ns	
Body to drain diode forward voltage	V_{DF}	_	-0.8	_	V	$I_F = -1 \text{ A, V}_{GS} = 0$
Body to drain diode reverse recovery time	t _{rr}	_	300	_	ns	$I_F = -1 \text{ A}, V_{GS} = 0,$ $di_F/dt = 100 \text{ A}/\mu\text{s}$

Note: 1. Pulse test

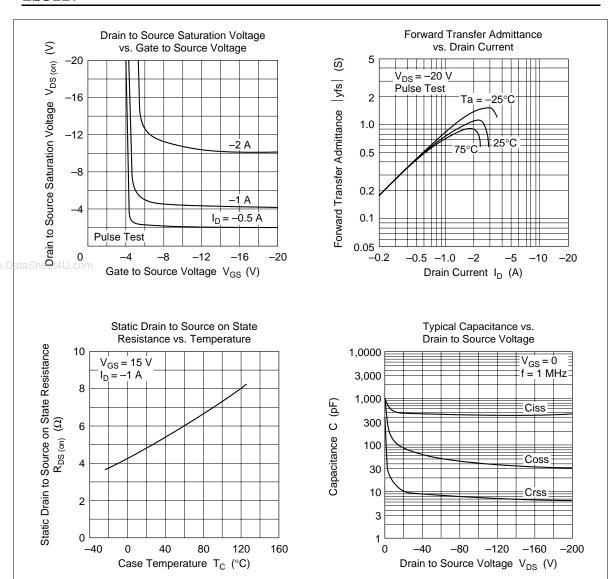


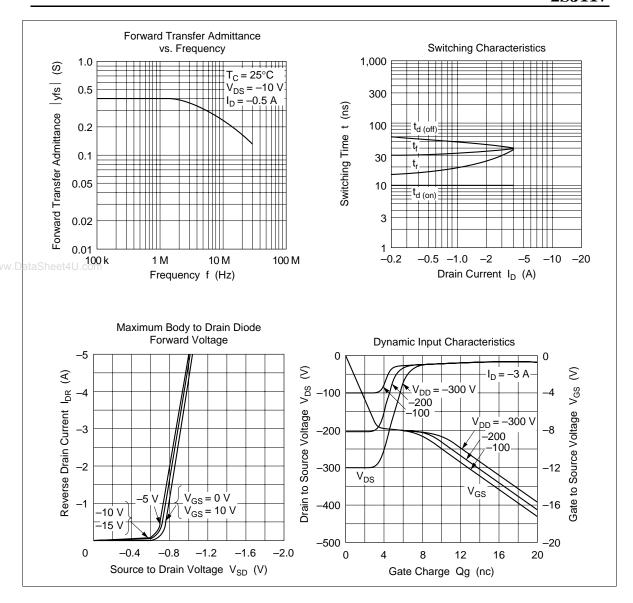




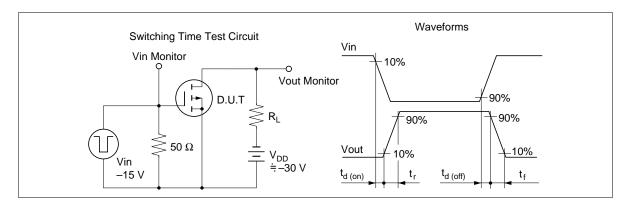


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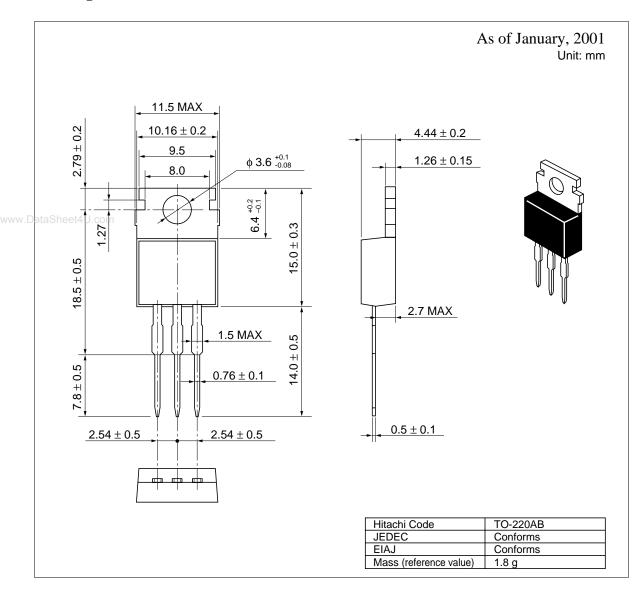


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Package Dimensions



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